IN THE CLAIMS

Please amend the claims as follows:

1. (Original) A heterojunction bipolar transistor, comprising:

a collector and a collector electrode formed within a silicon substrate;

base electrodes formed on the collector and including a protrusion having a first opening for exposing the surface of the collector and a body having a second opening for exposing the surface of the collector;

a base epitaxial layer grown selectively on the collector exposed through the first opening;

sidewall spacers formed on the sidewalls of the second opening and covering the protrusion;

an emitter electrode formed on the base epitaxial layer and having a shape of an overhang that covers the sidewall spacers; and

an insulation layer inserted between the overhang of the emitter electrode and the base electrodes and connected to the sidewall spacers.

2. (Original) The transistor as recited in claim 1, further comprising:

a buried collector area formed within the silicon substrate;

a collector epitaxial layer formed on the silicon substrate; and

a local silicon oxide layer formed on the collector epitaxial layer,

wherein the base electrodes are formed extended over the local silicon oxide layer and part of the collector, and the collector and the collector electrode are connected to each other through the buried collector area.

3. (Original) The transistor as recited in claim 1, wherein the base electrode is formed by integrating the silicon epitaxial layer on the collector and the polysilicon layer on the local silicon oxide layer.

4. (Original) The transistor as recited in claim 1, wherein the base epitaxial layer is formed of silicon-germanium alloy or silicon.

5. (Original) The transistor as recited in claim 1, wherein a silicide thin film is formed on the base electrode, the emitter electrode and the collector electrode.

6. (Original) The transistor as recited in claim 5, wherein insulation spacers are formed on both sidewalls of the emitter electrode meeting with the base electrodes in order to prevent the silicide thin film on the emitter electrode from contacting the base electrodes.

7. (Original) The transistor as recited in claim 1, wherein the sidewall spacers are formed of an oxide layer or a nitride layer, and the insulation layer is formed of an oxide layer.

8-13 (Cancelled)